



# BSS138BK

60 V, 360 mA N-channel Trench MOSFET

Rev. 1 — 4 August 2011

Product data sheet

## 1. Product profile

### 1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ESD protection up to 1.5 kV
- AEC-Q101 qualified

### 1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 1.4 Quick reference data

Table 1. Quick reference data

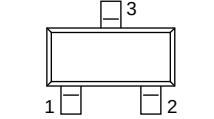
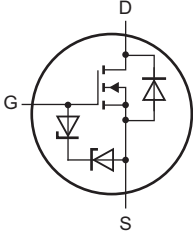
| Symbol                        | Parameter                        | Conditions                                                                    | Min   | Typ | Max | Unit     |
|-------------------------------|----------------------------------|-------------------------------------------------------------------------------|-------|-----|-----|----------|
| $V_{DS}$                      | drain-source voltage             | $T_j = 25\text{ }^{\circ}\text{C}$                                            | -     | -   | 60  | V        |
| $V_{GS}$                      | gate-source voltage              |                                                                               | -20   | -   | 20  | V        |
| $I_D$                         | drain current                    | $V_{GS} = 10\text{ V}; T_{amb} = 25\text{ }^{\circ}\text{C}$                  | [1] - | -   | 360 | mA       |
| <b>Static characteristics</b> |                                  |                                                                               |       |     |     |          |
| $R_{DS(on)}$                  | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 350\text{ mA}; T_j = 25\text{ }^{\circ}\text{C}$ | -     | 1   | 1.6 | $\Omega$ |

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline                                                                                    | Graphic symbol                                                                                   |
|-----|--------|-------------|-------------------------------------------------------------------------------------------------------|--------------------------------------------------------------------------------------------------|
| 1   | G      | gate        | <br>SOT23 (TO-236AB) | <br>017aaa255 |
| 2   | S      | source      |                                                                                                       |                                                                                                  |
| 3   | D      | drain       |                                                                                                       |                                                                                                  |

3. Ordering information

Table 3. Ordering information

| Type number | Package  |                                          |         |
|-------------|----------|------------------------------------------|---------|
|             | Name     | Description                              | Version |
| BSS138BK    | TO-236AB | plastic surface-mounted package; 3 leads | SOT23   |

4. Marking

Table 4. Marking codes

| Type number | Marking code <sup>[1]</sup> |
|-------------|-----------------------------|
| BSS138BK    | %SB                         |

[1] % = placeholder for manufacturing site code.

## 5. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol           | Parameter               | Conditions                                                     | Min   | Max  | Unit |
|------------------|-------------------------|----------------------------------------------------------------|-------|------|------|
| V <sub>DS</sub>  | drain-source voltage    | T <sub>j</sub> = 25 °C                                         | -     | 60   | V    |
| V <sub>GS</sub>  | gate-source voltage     |                                                                | -20   | 20   | V    |
| I <sub>D</sub>   | drain current           | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C               | [1] - | 360  | mA   |
|                  |                         | V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C              | [1] - | 230  | mA   |
| I <sub>DM</sub>  | peak drain current      | T <sub>amb</sub> = 25 °C; single pulse; t <sub>p</sub> ≤ 10 μs | -     | 1.2  | A    |
| P <sub>tot</sub> | total power dissipation | T <sub>amb</sub> = 25 °C                                       | [2] - | 350  | mW   |
|                  |                         |                                                                | [1] - | 420  | mW   |
|                  |                         | T <sub>sp</sub> = 25 °C                                        | -     | 1140 | mW   |
| T <sub>j</sub>   | junction temperature    |                                                                | -55   | 150  | °C   |
| T <sub>amb</sub> | ambient temperature     |                                                                | -55   | 150  | °C   |
| T <sub>stg</sub> | storage temperature     |                                                                | -65   | 150  | °C   |

### Source-drain diode

|                |                |                          |       |     |    |
|----------------|----------------|--------------------------|-------|-----|----|
| I <sub>S</sub> | source current | T <sub>amb</sub> = 25 °C | [1] - | 360 | mA |
|----------------|----------------|--------------------------|-------|-----|----|

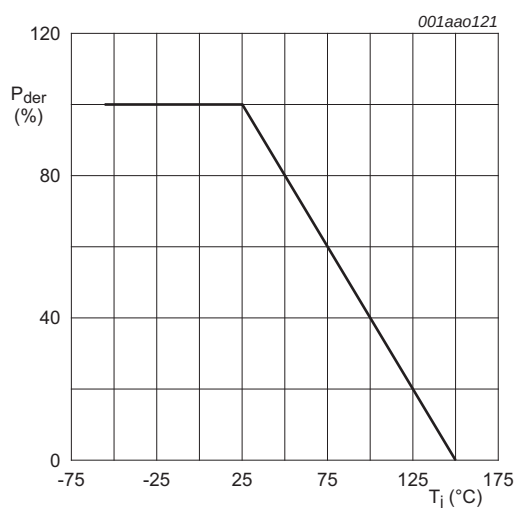
### ESD maximum rating

|                  |                                 |     |       |      |   |
|------------------|---------------------------------|-----|-------|------|---|
| V <sub>ESD</sub> | electrostatic discharge voltage | HBM | [3] - | 1500 | V |
|------------------|---------------------------------|-----|-------|------|---|

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

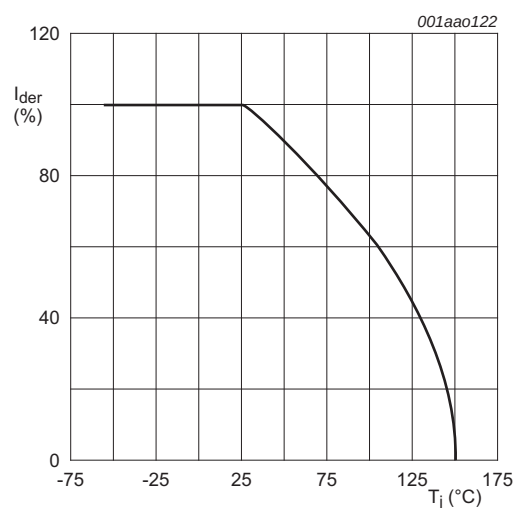
[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[3] Measured between all pins.



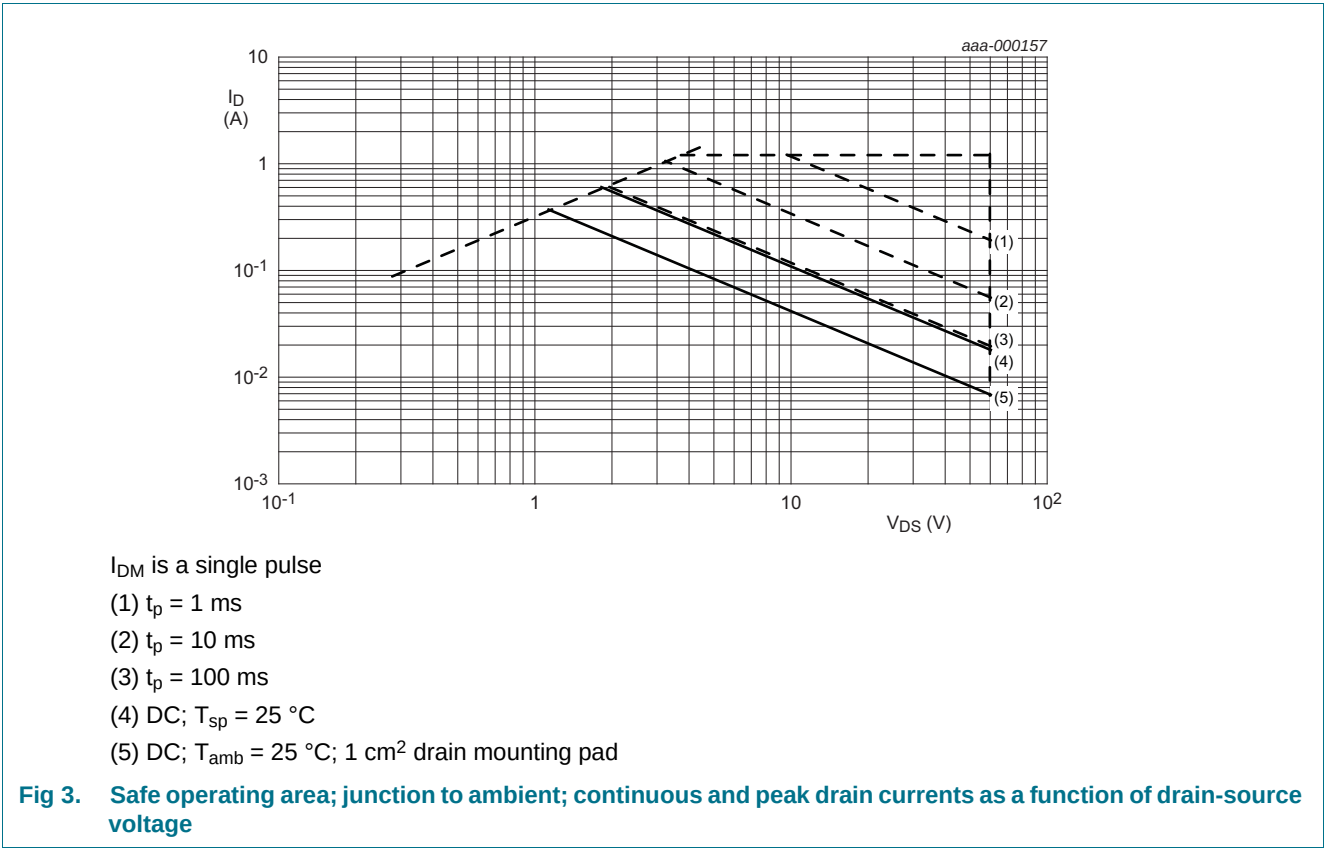
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}\text{C})}} \times 100\%$$

**Fig 1. Normalized total power dissipation as a function of junction temperature**



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100\%$$

**Fig 2. Normalized continuous drain current as a function of junction temperature**



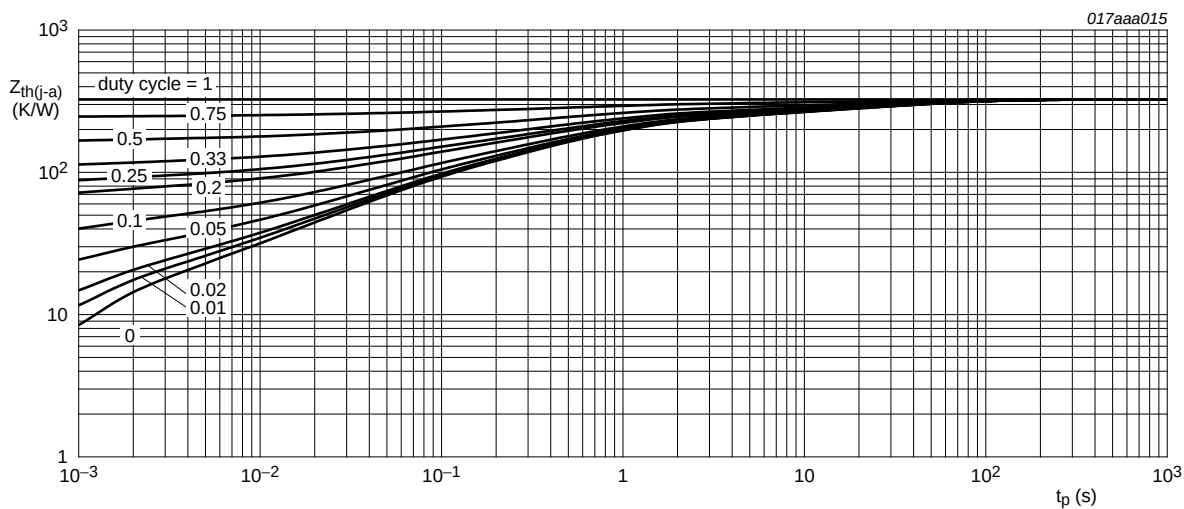
## 6. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter                                        | Conditions  | Min | Typ | Max | Unit |
|----------------|--------------------------------------------------|-------------|-----|-----|-----|------|
| $R_{th(j-a)}$  | thermal resistance from junction to ambient      | in free air | [1] | -   | 310 | K/W  |
|                |                                                  |             | [2] | -   | 260 | K/W  |
| $R_{th(j-sp)}$ | thermal resistance from junction to solder point | -           | -   | -   | 115 | K/W  |

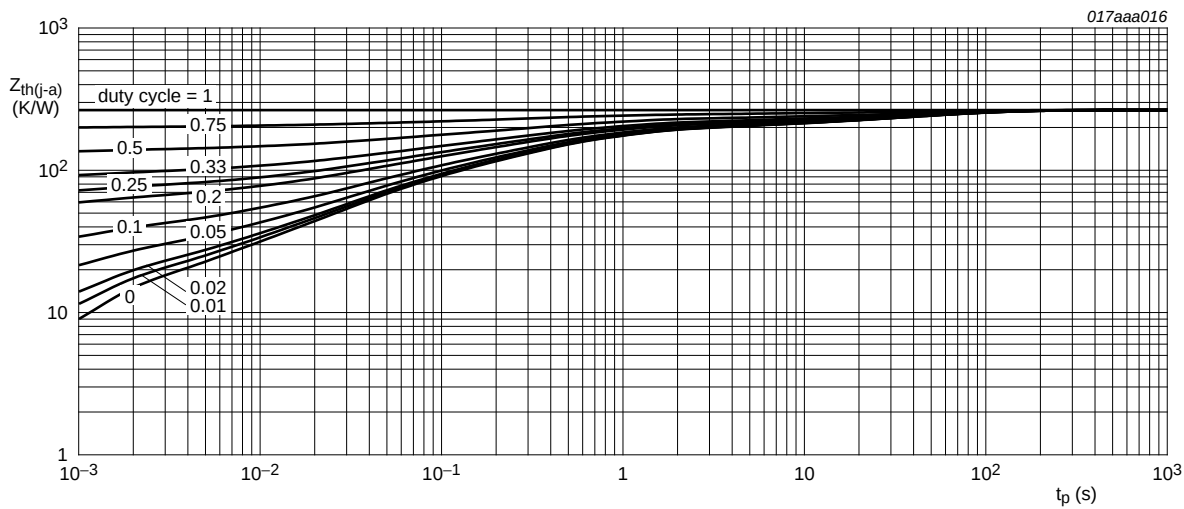
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain  $1\text{ cm}^2$ .



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 1 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

## 7. Characteristics

Table 7. Characteristics

| Symbol                         | Parameter                        | Conditions                                                                                                                         | Min  | Typ | Max | Unit          |
|--------------------------------|----------------------------------|------------------------------------------------------------------------------------------------------------------------------------|------|-----|-----|---------------|
| <b>Static characteristics</b>  |                                  |                                                                                                                                    |      |     |     |               |
| $V_{(BR)DSS}$                  | drain-source breakdown voltage   | $I_D = 250\ \mu\text{A}$ ; $V_{GS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                     | 60   | -   | -   | V             |
| $V_{GSth}$                     | gate-source threshold voltage    | $I_D = 250\ \mu\text{A}$ ; $V_{DS} = V_{GS}$ ; $T_j = 25\ ^\circ\text{C}$                                                          | 0.48 | 1.1 | 1.6 | V             |
| $I_{DSS}$                      | drain leakage current            | $V_{DS} = 60\ \text{V}$ ; $V_{GS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                      | -    | -   | 1   | $\mu\text{A}$ |
|                                |                                  | $V_{DS} = 60\ \text{V}$ ; $V_{GS} = 0\ \text{V}$ ; $T_j = 150\ ^\circ\text{C}$                                                     | -    | -   | 10  | $\mu\text{A}$ |
| $I_{GSS}$                      | gate leakage current             | $V_{GS} = 20\ \text{V}$ ; $V_{DS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                      | -    | -   | 10  | $\mu\text{A}$ |
|                                |                                  | $V_{GS} = -20\ \text{V}$ ; $V_{DS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                     | -    | -   | 10  | $\mu\text{A}$ |
|                                |                                  | $V_{GS} = 10\ \text{V}$ ; $V_{DS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                      | -    | -   | 1   | $\mu\text{A}$ |
|                                |                                  | $V_{GS} = -10\ \text{V}$ ; $V_{DS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                     | -    | -   | 1   | $\mu\text{A}$ |
| $R_{DSon}$                     | drain-source on-state resistance | $V_{GS} = 10\ \text{V}$ ; $I_D = 350\ \text{mA}$ ; $T_j = 25\ ^\circ\text{C}$                                                      | -    | 1   | 1.6 | $\Omega$      |
|                                |                                  | $V_{GS} = 10\ \text{V}$ ; $I_D = 350\ \text{mA}$ ; $T_j = 150\ ^\circ\text{C}$                                                     | -    | 2   | 3.2 | $\Omega$      |
|                                |                                  | $V_{GS} = 4.5\ \text{V}$ ; $I_D = 200\ \text{mA}$ ; $T_j = 25\ ^\circ\text{C}$                                                     | -    | 1.1 | 2.2 | $\Omega$      |
|                                |                                  | $V_{GS} = 2.5\ \text{V}$ ; $I_D = 10\ \text{mA}$ ; $T_j = 25\ ^\circ\text{C}$                                                      | -    | 1.4 | 6.5 | $\Omega$      |
| $g_{fs}$                       | forward transconductance         | $V_{DS} = 10\ \text{V}$ ; $I_D = 200\ \text{mA}$ ; $T_j = 25\ ^\circ\text{C}$                                                      | -    | 700 | -   | mS            |
| <b>Dynamic characteristics</b> |                                  |                                                                                                                                    |      |     |     |               |
| $Q_{G(tot)}$                   | total gate charge                | $V_{DS} = 30\ \text{V}$ ; $I_D = 300\ \text{mA}$ ; $V_{GS} = 4.5\ \text{V}$ ;<br>$T_j = 25\ ^\circ\text{C}$                        | -    | 0.6 | 0.7 | nC            |
| $Q_{GS}$                       | gate-source charge               |                                                                                                                                    | -    | 0.1 | -   | nC            |
| $Q_{GD}$                       | gate-drain charge                |                                                                                                                                    | -    | 0.2 | -   | nC            |
| $C_{iss}$                      | input capacitance                | $V_{DS} = 10\ \text{V}$ ; $f = 1\ \text{MHz}$ ; $V_{GS} = 0\ \text{V}$ ;<br>$T_j = 25\ ^\circ\text{C}$                             | -    | 42  | 56  | pF            |
| $C_{oss}$                      | output capacitance               |                                                                                                                                    | -    | 7   | -   | pF            |
| $C_{rss}$                      | reverse transfer capacitance     |                                                                                                                                    | -    | 4   | -   | pF            |
| $t_{d(on)}$                    | turn-on delay time               | $V_{DS} = 40\ \text{V}$ ; $R_L = 250\ \Omega$ ; $V_{GS} = 10\ \text{V}$ ;<br>$R_{G(ext)} = 6\ \Omega$ ; $T_j = 25\ ^\circ\text{C}$ | -    | 5   | 10  | ns            |
| $t_r$                          | rise time                        |                                                                                                                                    | -    | 5   | -   | ns            |
| $t_{d(off)}$                   | turn-off delay time              |                                                                                                                                    | -    | 38  | 76  | ns            |
| $t_f$                          | fall time                        |                                                                                                                                    | -    | 20  | -   | ns            |
| <b>Source-drain diode</b>      |                                  |                                                                                                                                    |      |     |     |               |
| $V_{SD}$                       | source-drain voltage             | $I_S = 300\ \text{mA}$ ; $V_{GS} = 0\ \text{V}$ ; $T_j = 25\ ^\circ\text{C}$                                                       | 0.47 | 0.8 | 1.2 | V             |

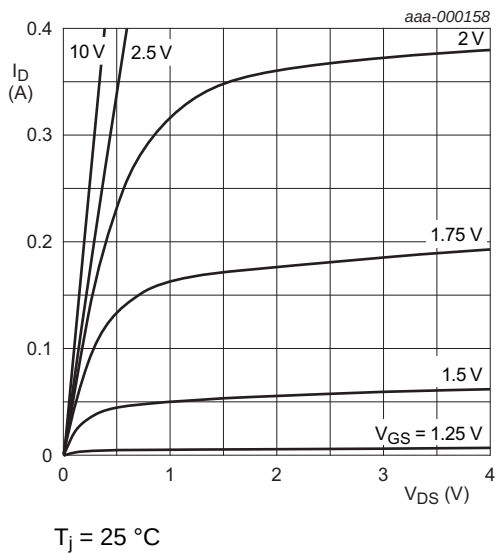


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values

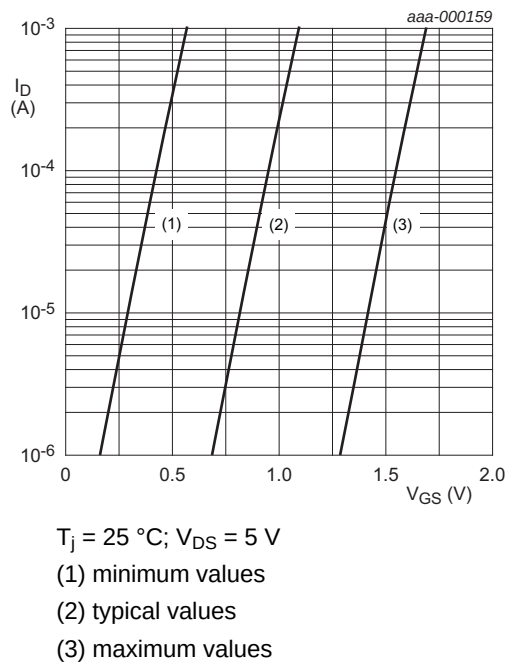


Fig 7. Sub-threshold drain current as a function of gate-source voltage

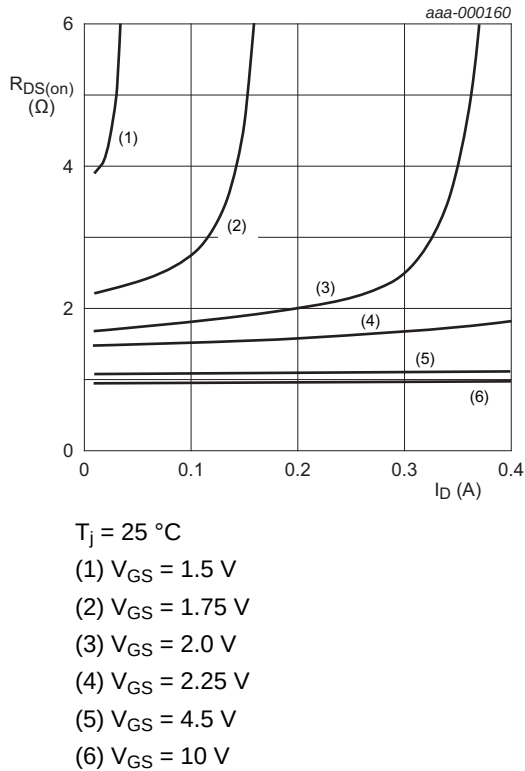


Fig 8. Drain-source on-state resistance as a function of drain current; typical values

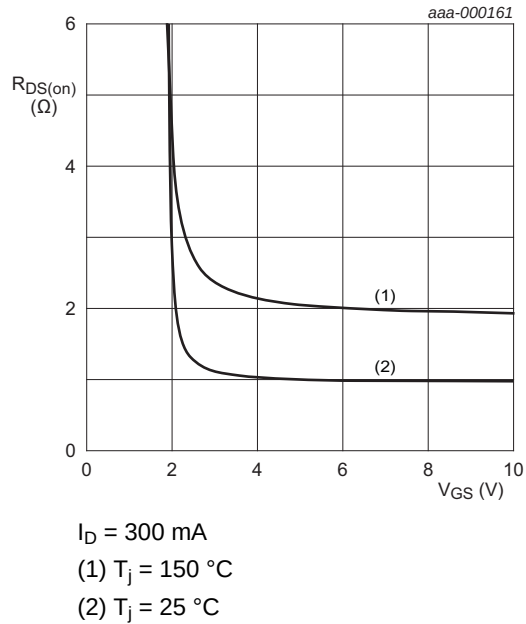
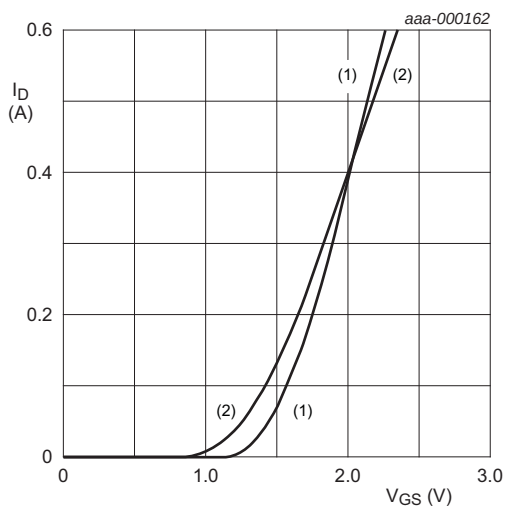
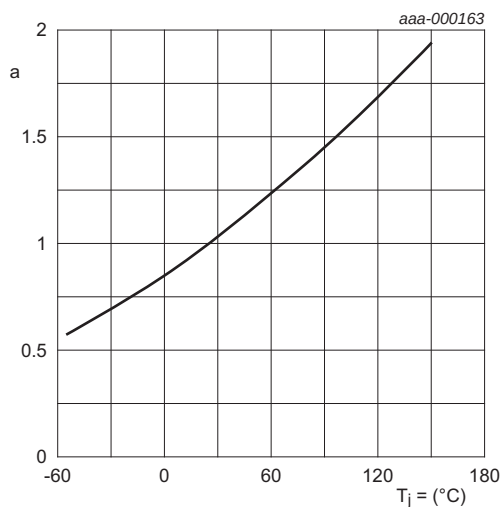


Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



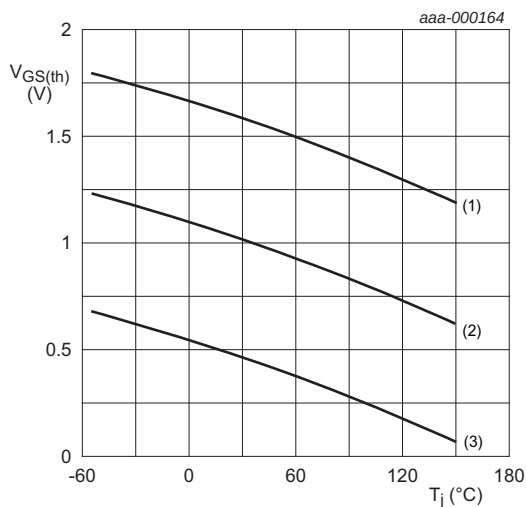
$V_{DS} > I_D \times R_{DSon}$   
(1)  $T_j = 25\text{ }^{\circ}\text{C}$   
(2)  $T_j = 150\text{ }^{\circ}\text{C}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



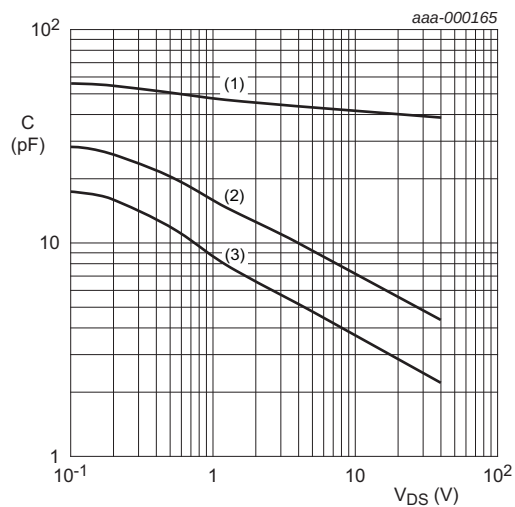
$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



$I_D = 0.25\text{ mA}$ ;  $V_{DS} = V_{GS}$   
(1) maximum values  
(2) typical values  
(3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



$f = 1\text{ MHz}$ ;  $V_{GS} = 0\text{ V}$   
(1)  $C_{iss}$   
(2)  $C_{oss}$   
(3)  $C_{rss}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



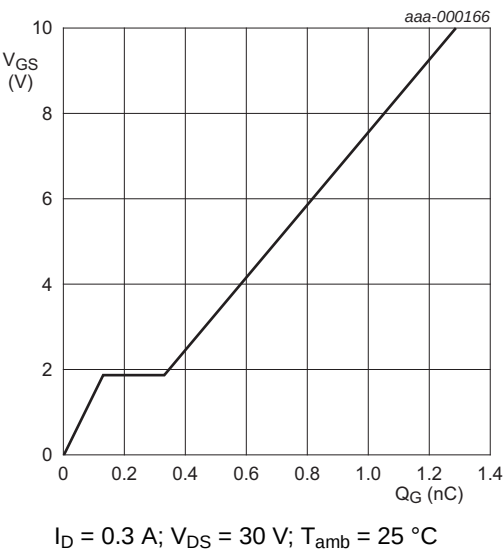


Fig 14. Gate-source voltage as a function of gate charge; typical values

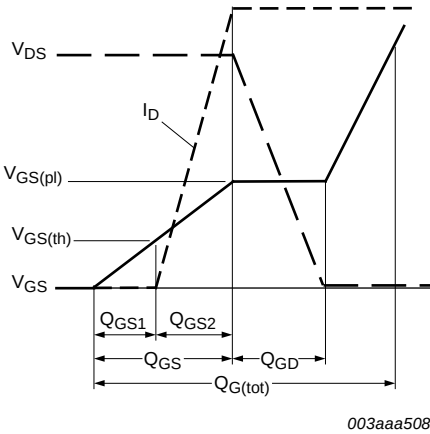
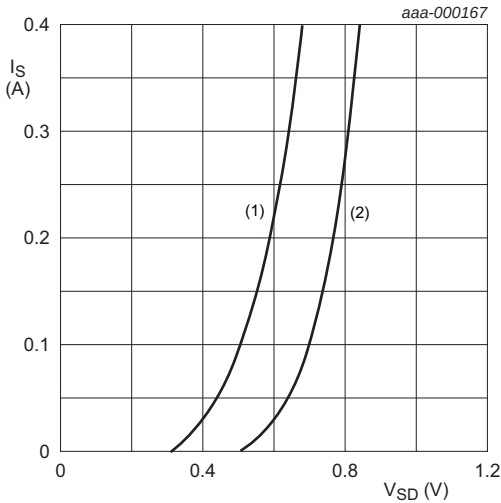


Fig 15. Gate charge waveform definitions



$V_{GS} = 0\text{ V}$   
 (1)  $T_j = 150\text{ }^{\circ}\text{C}$   
 (2)  $T_j = 25\text{ }^{\circ}\text{C}$

Fig 16. Source current as a function of source-drain voltage; typical values

## 8. Test information

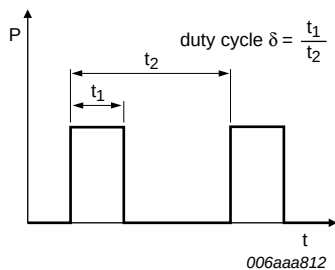


Fig 17. Duty cycle definition

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

Plastic surface-mounted package; 3 leadsSOT23

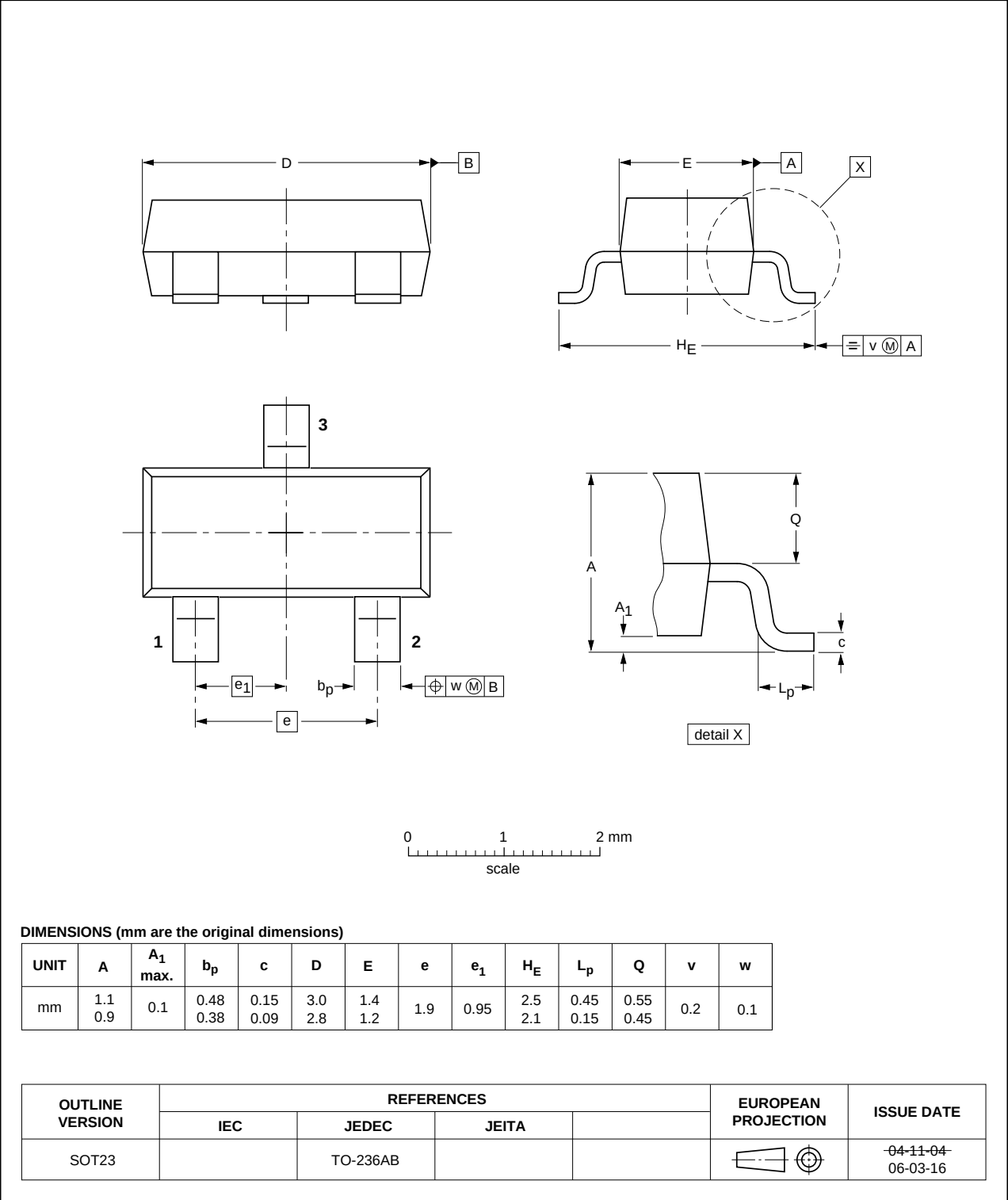


Fig 18. Package outline SOT23 (TO-236AB)

10. Soldering

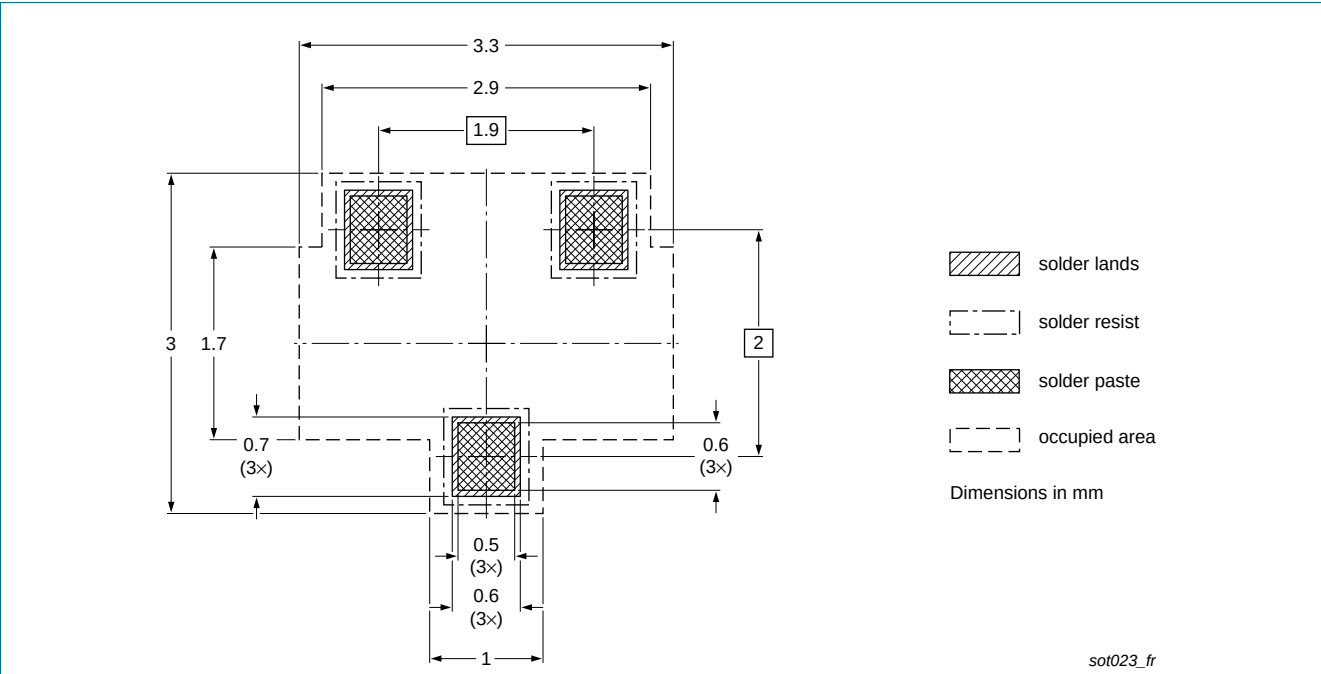


Fig 19. Reflow soldering footprint for SOT23 (TO-236AB)

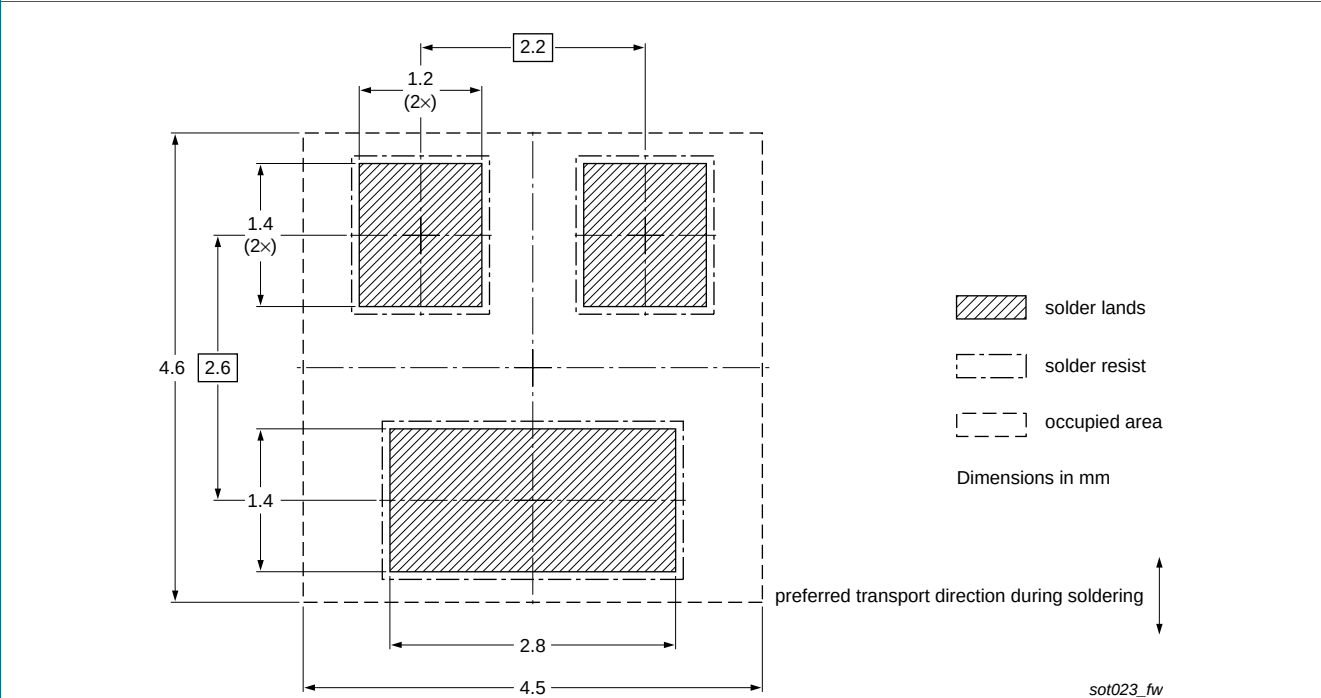


Fig 20. Wave soldering footprint for SOT23 (TO-236AB)

## 11. Revision history

Table 8. Revision history

| Document ID  | Release date | Data sheet status  | Change notice | Supersedes |
|--------------|--------------|--------------------|---------------|------------|
| BSS138BK v.1 | 20110804     | Product data sheet | -             | -          |

## 12. Legal information

### 12.1 Data sheet status

| Document status <sup>[1] [2]</sup> | Product status <sup>[3]</sup> | Definition                                                                            |
|------------------------------------|-------------------------------|---------------------------------------------------------------------------------------|
| Objective [short] data sheet       | Development                   | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet     | Qualification                 | This document contains data from the preliminary specification.                       |
| Product [short] data sheet         | Production                    | This document contains the product specification.                                     |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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## 14. Contents

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